

Docket No.: 4459-050



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Jen-Kuang FANG et al.

Application No. 09/883,216

: Group Art Unit: 2811

Filed: June 19, 2001

: Examiner: Nitin Parekh

For: SEMICONDUCTOR DEVICE HAVING BUMP ELECTRODES

AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

The following amendments and remarks are submitted in response to the Official Action dated March 19, 2003.

IN THE CLAIMS:

✓ Please cancel claims 5-6 without prejudice or disclaimer.

Please amend the remaining claims as follows:

1. (Amended) A method of forming a semiconductor device having a bump electrode, the method comprising the steps of:

A1 providing an aluminum contact pad on a substrate, at least a portion of the aluminum contact pad being exposed through a dielectric layer on the substrate;

forming an aluminum layer on the dielectric layer and the portion of the aluminum contact pad exposed through the dielectric layer;

forming a nickel-vanadium layer on the aluminum layer;

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